

TrenchMV™ Power MOSFET

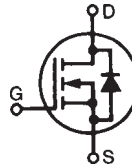
IXTP55N075T IXTY55N075T

$$V_{DSS} = 75 \text{ V}$$

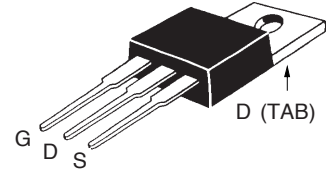
$$I_{D25} = 55 \text{ A}$$

$$R_{DS(on)} \leq 19.5 \text{ m}\Omega$$

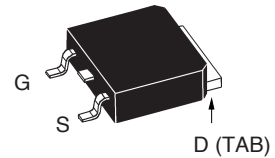
N-Channel Enhancement Mode
Avalanche Rated



TO-220 (IXTP)



TO-252 (IXTY)



G = Gate D = Drain
S = Source TAB = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 175°C | 75 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$ | 75 | V |
| V_{GSM} | Transient | ± 20 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 55 | A |
| I_L | Package Current Limit, RMS TO-252 | 25 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 150 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 10 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 250 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 18 \Omega$ | 3 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 130 | W |
| T_J | | -55 ... +175 | $^\circ\text{C}$ |
| T_{JM} | | 175 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +175 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic body for 10 seconds | 260 | $^\circ\text{C}$ |
| M_d | Mounting torque (TO-220) | 1.13 / 10 | Nm/lb.in. |
| Weight | TO-220 | 3 | g |
| | TO-252 | 0.35 | g |

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- 175 $^\circ\text{C}$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 42V Power Bus
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- High Current Switching Applications

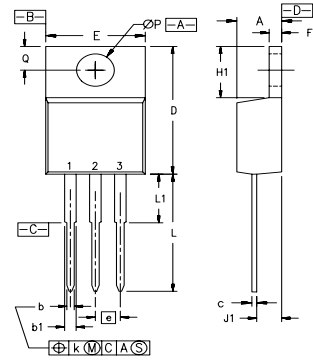
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-----------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$ | 75 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 25 \mu\text{A}$ | 2.0 | | 4.0 V |
| I_{GSS} | $V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ | | | $\pm 100 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 1 μA |
| | $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$ | | | 100 μA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Notes 1, 2 | | | 19.5 $\text{m}\Omega$ |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|-----------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$, Note 1 | 16 | 27 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 1400 | pF |
| C_{oss} | | 235 | pF | |
| C_{rss} | | 123 | pF | |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 10\text{ A}$ $R_G = 18\ \Omega$ (External) | | 20 | ns |
| t_r | | 50 | ns | |
| $t_{d(off)}$ | | 44 | ns | |
| t_f | | 41 | ns | |
| $Q_{g(on)}$ | | | 33 | nC |
| Q_{gs} | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 10\text{ A}$ | | 10 | nC |
| Q_{gd} | | | 9 | nC |
| R_{thJC} | TO-220 | | | 1.15 °C/W |
| R_{thCS} | | 0.5 | °C/W | |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|----------|--|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 55 A |
| I_{SM} | Repetitive | | | 150 A |
| V_{SD} | $I_F = 25\text{ A}, V_{GS} = 0\text{ V}$, Note 1 | | | 1.2 V |
| t_{rr} | $I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 40\text{ V}, V_{GS} = 0\text{ V}$ | | 50 | ns |

TO-220 (IXTP) Outline

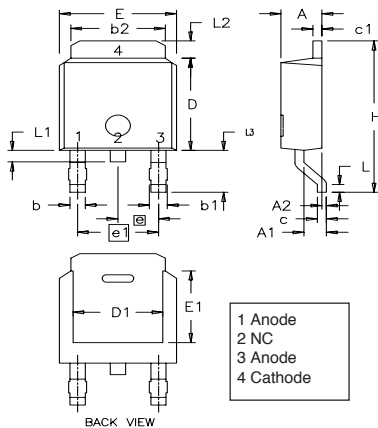


| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .190 | 4.32 | 4.83 |
| b | .025 | .040 | 0.64 | 1.02 |
| b1 | .045 | .065 | 1.15 | 1.65 |
| c | .014 | .022 | 0.35 | 0.56 |
| D | .580 | .630 | 14.73 | 16.00 |
| E | .390 | .420 | 9.91 | 10.66 |
| e | .100 BSC | | 2.54 BSC | |
| F | .045 | .055 | 1.14 | 1.40 |
| H1 | .230 | .270 | 5.85 | 6.85 |
| J1 | .090 | .110 | 2.29 | 2.79 |
| k | 0 | .015 | 0 | 0.38 |
| L | .500 | .550 | 12.70 | 13.97 |
| L1 | .110 | .230 | 2.79 | 5.84 |
| ØP | .139 | .161 | 3.53 | 4.08 |
| Q | .100 | .125 | 2.54 | 3.18 |

Notes:

- Pulse test: $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$;
- On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5 mm or less from the package body.

TO-252 (IXTY) Outline



| Dim. | Millimeter | | Inches | |
|------|------------|-------|-----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.19 | 2.38 | 0.086 | 0.094 |
| A1 | 0.89 | 1.14 | 0.035 | 0.045 |
| A2 | 0 | 0.13 | 0 | 0.005 |
| b | 0.64 | 0.89 | 0.025 | 0.035 |
| b1 | 0.76 | 1.14 | 0.030 | 0.045 |
| b2 | 5.21 | 5.46 | 0.205 | 0.215 |
| c | 0.46 | 0.58 | 0.018 | 0.023 |
| c1 | 0.46 | 0.58 | 0.018 | 0.023 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.32 | 5.21 | 0.170 | 0.205 |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | 5.21 | 0.170 | 0.205 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.57 BSC | | 0.180 BSC | |
| H | 9.40 | 10.42 | 0.370 | 0.410 |
| L | 0.51 | 1.02 | 0.020 | 0.040 |
| L1 | 0.64 | 1.02 | 0.025 | 0.040 |
| L2 | 0.89 | 1.27 | 0.035 | 0.050 |
| L3 | 2.54 | 2.92 | 0.100 | 0.115 |

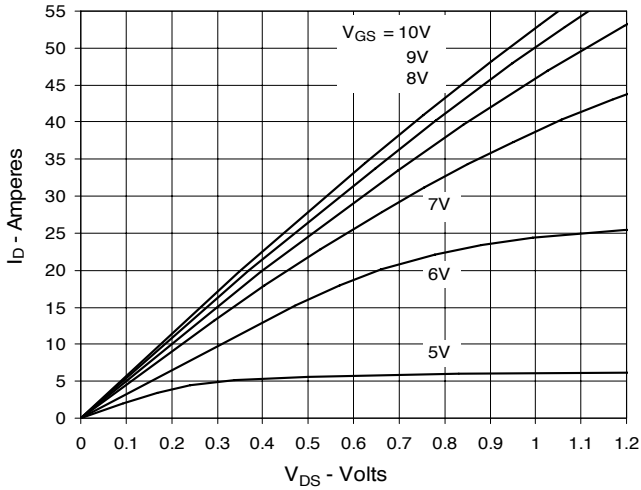
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

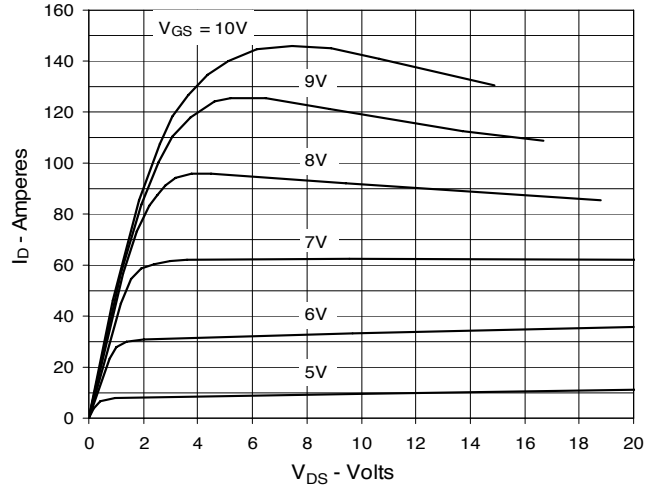
IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 |

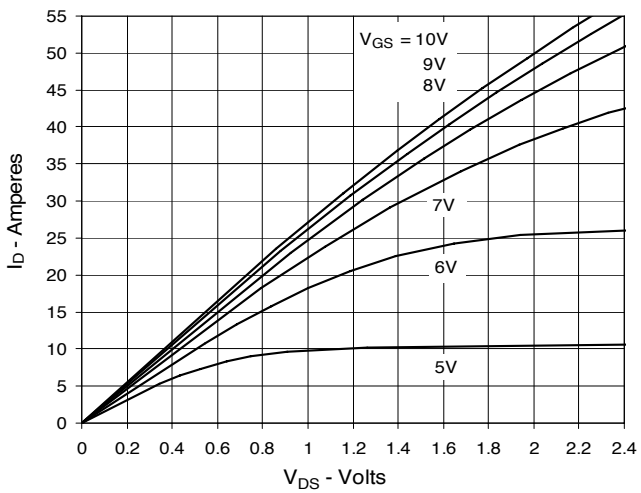
**Fig. 1. Output Characteristics
@ 25°C**



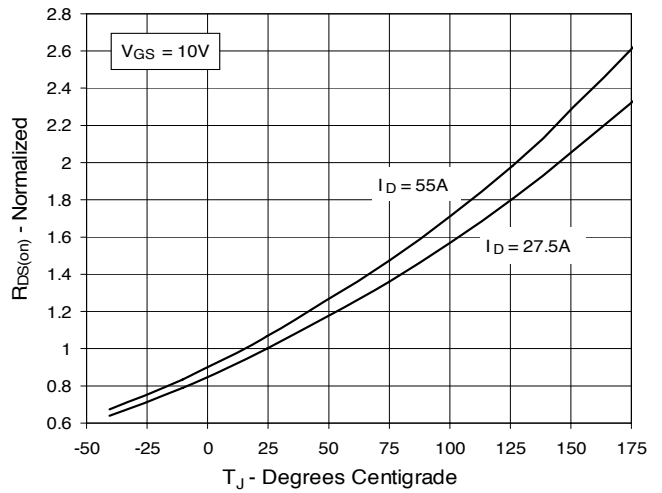
**Fig. 2. Extended Output Characteristics
@ 25°C**



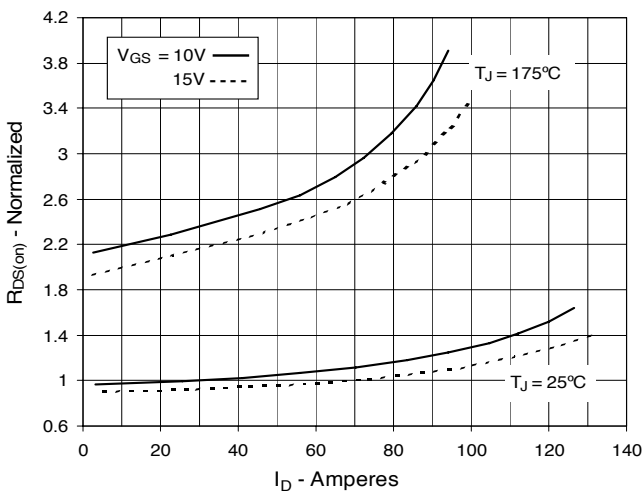
**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 27.5A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 27.5A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

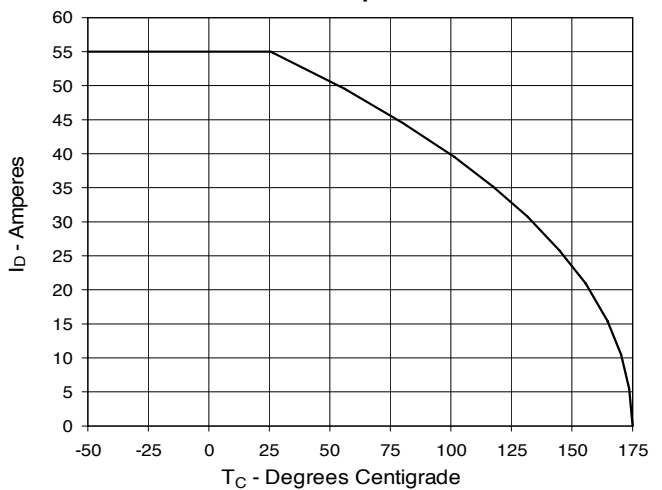


Fig. 7. Input Admittance

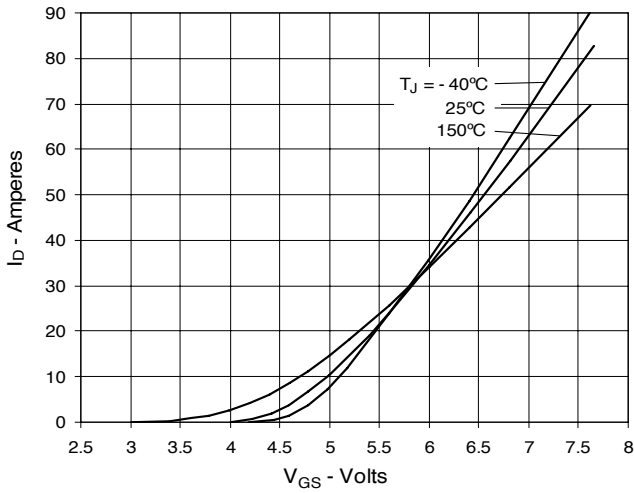


Fig. 8. Transconductance

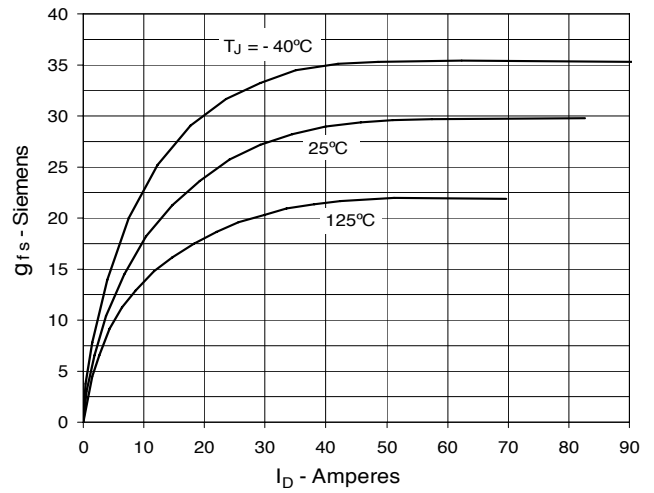


Fig. 9. Forward Voltage Drop of Intrinsic Diode

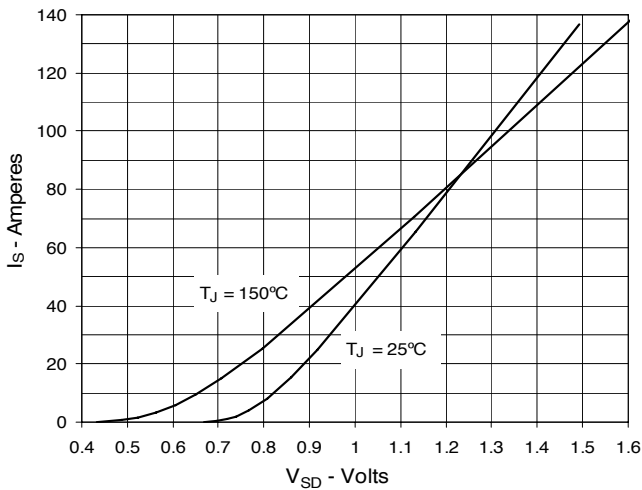


Fig. 10. Gate Charge

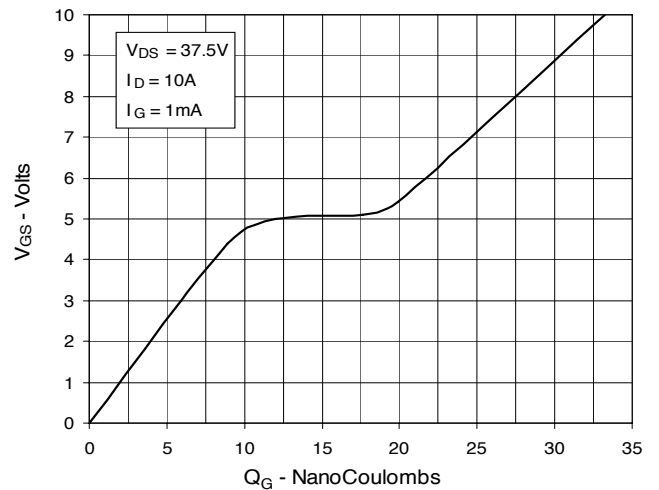


Fig. 11. Capacitance

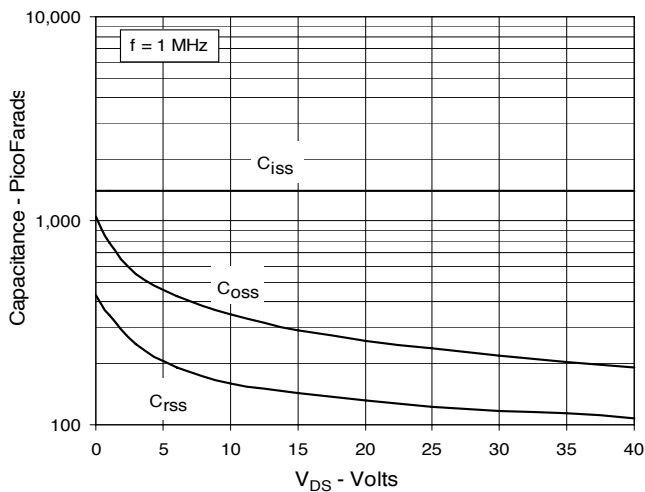
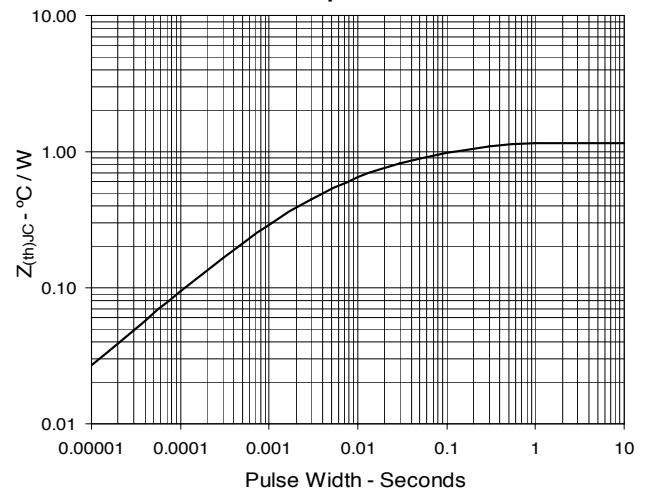
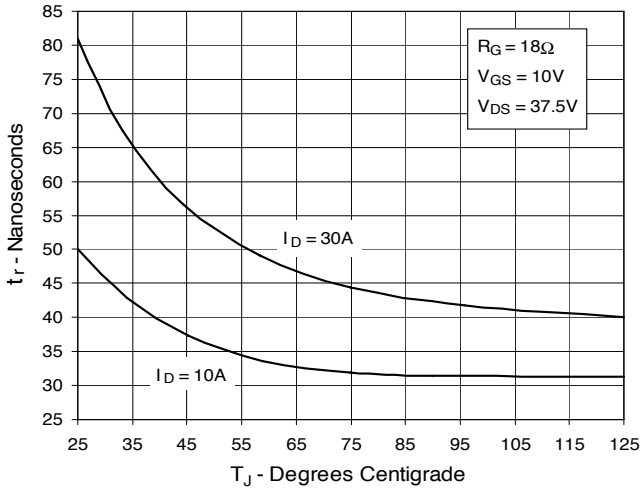


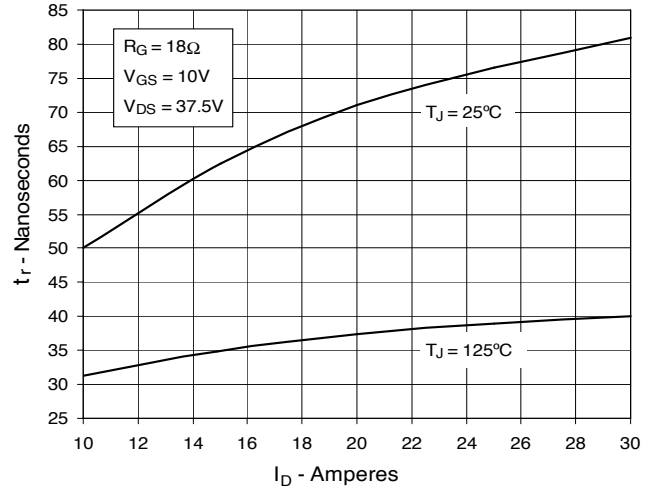
Fig. 12. Maximum Transient Thermal Impedance



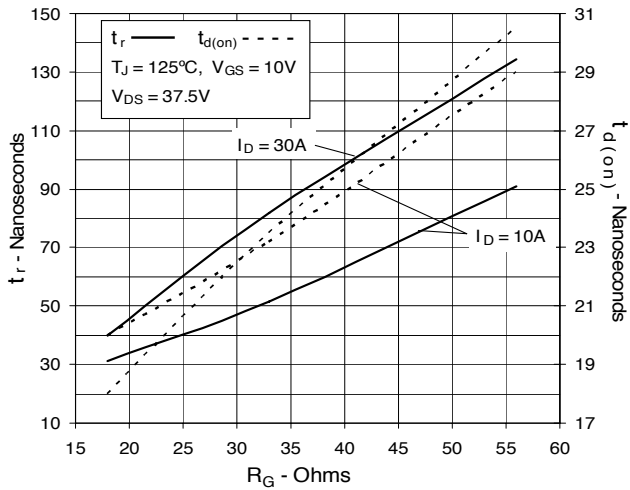
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



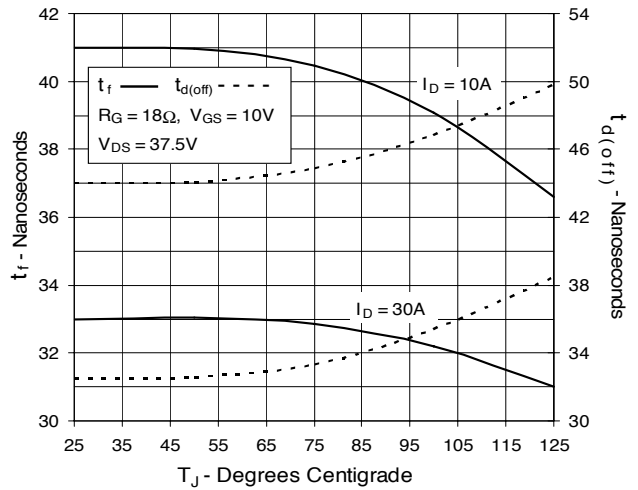
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



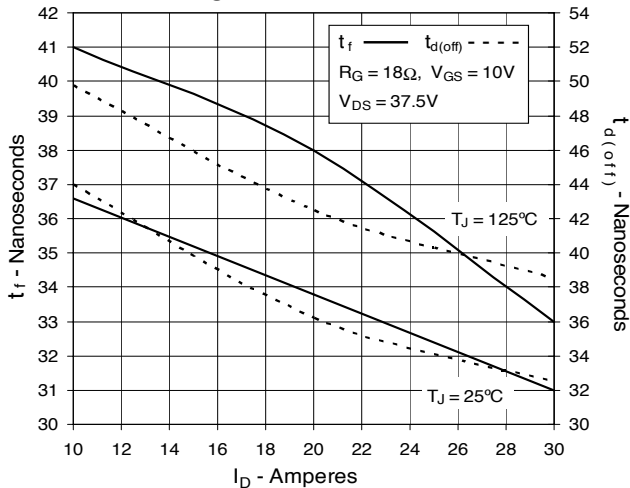
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

